

74LCX646

LOW VOLT. CMOS OCTAL BUS TRANSCEIVER/REGISTER WITH 5 VOLT TOLERANT INPUTS AND OUTPUTS(3-STATE)

- 5V TOLERANT INPUTS AND OUTPUTS
- HIGH SPEED: t_{PD} = 7.0 ns (MAX.) at V_{CC} = 3V
- POWER DOWN PROTECTION ON INPUTS AND OUTPUTS
- SYMMETRICAL OUTPUT IMPEDANCE: |I_{OH}| = I_{OL} = 24mA (MIN) at V_{CC} = 3V
- PCI BUS LEVELS GUARANTEED AT 24 mA
- BALANCED PROPAGATION DELAYS: t_{PLH} ≅ t_{PHL}
- OPERATING VOLTAGE RANGE: V_{CC}(OPR) = 2.0V to 3.6V (1.5V Data Retention)
- PIN AND FUNCTION COMPATIBLE WITH 74 SERIES 646
- LATCH-UP PERFORMANCE EXCEEDS 500mA (JESD 17)
- ESD PERFORMANCE: HBM > 2000V (MIL STD 883 method 3015); MM > 200V

DESCRIPTION

The 74LCX646 is a low voltage CMOS OCTAL BUS TRANSCEIVER AND REGISTER (3-STATE) fabricated with sub-micron silicon gate and double-layer metal wiring C²MOS technology. It is ideal for low power and high speed 3.3V applications; it can be interfaced to 5V signal environment for both inputs and outputs.



Table 1: Order Codes

PACKAGE	T & R
SOP	74LCX646RM13TR
TSSOP	74LCX646TTR

This device consists of bus transceiver circuits with 3 state, D-type flip-flops, and control circuitry arranged for multiplexed transmission of data directly from the input bus or from the internal registers. Data on the A or B bus will be clocked into register on the low to high transition of the appropriate clock pin (Clock AB or Clock BA). Enable (G) and direction (DIR) pins are provided to control the transceiver functions. In the transceiver mode, data present at the high-impedance port may be stored in either register or in both. The select controls (Select AB select BA) can multiplex stored and real time (transparent mode) data. The direction control determines which bus will receive data when enable \overline{G} is active (low). In the isolation mode



(enable \overline{G} high), "A" data may be stored in one register and/or "B" data may be stored in the other register. When an output function is disabled, the input function is still enabled and may be used to store and transmit data. Only one of the two buses, A or B, may be driven at a time. It has same speed performance at 3.3V than 5V

Figure 2: Input And Output Equivalent Circuit

AC/ACT family, combined with a lower power consumption.

All inputs and outputs are equipped with protection circuits against static discharge, giving them 2KV ESD immunity and transient excess voltage.



Table 2: Pin Description

PIN N°	SYMBOL	NAME AND FUNCTION
1	CLOCK AB (CAB)	A to B Clock Input (LOW to HIGH, Edge-Triggered)
2	SELECT AB (SAB)	Select A to B Source Input
3	DIR	Direction Control Input
4, 5, 6, 7, 8, 9, 10, 11	A1 to A8	A Data Inputs/Outputs
20, 19, 18, 17, 16, 15, 14, 13	B1 to B8	B Data Inputs/Outputs
21	G	Output Enable Input (Active LOW)
22	SELECT BA (SBA)	Select B to A Source Input
23	CLOCK BA (CBA)	B to A Clock Input (LOW to HIGH, Edge Triggered)
12	GND	Ground (0V)
24	V _{CC}	Positive Supply Voltage

Table 3: Truth Table

G	DIR	САВ	СВА	SAB	SBA	Α	В	FUNCTION
						INPUTS	INPUTS	Both the A bus and the B bus are inputs
		Х	Х	Х	Х	Z	Z	The Output functions of the A and B bus are disabled
Н	Х			х	х	INPUTS	INPUTS	Both the A and B bus are used as inputs to the internal flip-flops. Data at the bus will be stored on low to high transition of the clock inputs.
						INPUTS	OUTPUTS	The A bus are inputs and the B bus are outputs
		х	Х*	L	х	L	L	The data at the A bus are displayed at the B bus
		^	~	L	^	Н	Н	The data at the A bus are displayed at the b bus
		_				L	L	The data at the A bus are displayed at the B bus. The
L	н		Х*	L	Х	Н	Н	data of the A bus are stored to internal flip-flop on low to high transition of the clock pulse
		х	Х*	н	х	Х	Qn	The data stored to the internal flip-flop are displayed at the B bus.
						L	L	The data at the A bus are stored to the internal flip-flop
			Х*	Н	Х	Н	Н	on low to high transition of the clock pulse. The states of the internal flip-flops output directly to the B bus.
						OUTPUTS	INPUTS	The B bus are inputs and the A bus are outputs.
		Х*	х	х	L	L	L	The data at the B bus are displayed at the A bus
		^	~	~		Н	Н	The data at the b bus are displayed at the A bus
) (th	_			L	L	The data at the B bus are displayed at the A bus. The
L	L	Х*		Х	L	Н	Н	data of the B bus are stored to the internal flip-flop on low to high transition of the clock pulse.
		Х*	Х	х	Н	Qn	Х	The data stored to the internal flip-flops are displayed at the A bus
			_			L	L	The data at the B bus are stored to the internal flip-flop
		Х*		Х	Н			on low to high transition of the clock pulse. The states of the internal flip-flops output directly to the A bus.

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X : Don't Care Z : High Impedance

Qn: The data stored to the internal flip-flops by most recent low to high transition of the clock inputs
 * : The data at the A and B bus will be stored to the internal flip-flops on every low to high transition of the clock inputs.

Figure 3: Logic Diagram



This logic diagram has not be used to estimate propagation delays

Figure 4: Timing Chart



Table 4: Absolute Maximum Ratings

Symbol	Parameter	Value	Unit
V _{CC}	Supply Voltage	-0.5 to +7.0	V
VI	DC Input Voltage	-0.5 to +7.0	V
Vo	DC Output Voltage (OFF State)	-0.5 to +7.0	V
Vo	DC Output Voltage (High or Low State) (note 1)	-0.5 to V _{CC} + 0.5	V
Ι _{ΙΚ}	DC Input Diode Current	- 50	mA
I _{OK}	DC Output Diode Current (note 2)	- 50	mA
Ι _Ο	DC Output Current	± 50	mA
I _{CC}	DC Supply Current per Supply Pin	± 100	mA
I _{GND}	DC Ground Current per Supply Pin	± 100	mA
T _{stg}	Storage Temperature	-65 to +150	°C
ΤL	Lead Temperature (10 sec)	300	°C

Absolute Maximum Ratings are those values beyond which damage to the device may occur. Functional operation under these conditions is not implied

1) I_O absolute maximum rating must be observed 2) V_O < GND

Table 5: Recommended Operating Conditions

Symbol	Parameter	Value	Unit
V _{CC}	Supply Voltage (note 1)	2.0 to 3.6	V
VI	Input Voltage	0 to 5.5	V
Vo	Output Voltage (OFF State)	0 to 5.5	V
Vo	Output Voltage (High or Low State)	0 to V _{CC}	V
I _{OH} , I _{OL}	High or Low Level Output Current (V _{CC} = 3.0 to 3.6V)	± 24	mA
I _{OH} , I _{OL}	High or Low Level Output Current (V _{CC} = 2.7V)	± 12	mA
T _{op}	Operating Temperature	-55 to 125	°C
dt/dv	Input Rise and Fall Time (note 2)	0 to 10	ns/V

1) Truth Table guaranteed: 1.5V to 3.6V 2) V_{IN} from 0.8V to 2V at V_{CC} = 3.0V

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Table 6: DC Specifications

		Те	est Condition		Va	alue		
Symbol	Parameter	v _{cc}		-40 to 85 °C		-55 to 1	125 °C	Unit
		(Ŭ)		Min.	Max.	Min.	Max.	
V _{IH}	High Level Input Voltage	- 2.7 to 3.6		2.0		2.0		V
V _{IL}	Low Level Input Voltage	2.7 10 3.0			0.8		0.8	V
V _{OH}	High Level Output	2.7 to 3.6	I _O =-100 μA	V _{CC} -0.2		V _{CC} -0.2		
	Voltage	2.7	I _O =-12 mA	2.2		2.2		v
		3.0	I _O =-18 mA	2.4		2.4		v
			I _O =-24 mA	2.2		2.2		
V _{OL}	V _{OL} Low Level Output	2.7 to 3.6	I _O =100 μA		0.2		0.2	
	Voltage	2.7	I _O =12 mA		0.4		0.4	v
		0.0	I _O =16 mA		0.4		0.4	V
		3.0	I _O =24 mA		0.55		0.55	
Ι _Ι	Input Leakage Current	2.7 to 3.6	V _I = 0 to 5.5V		± 5		±5	μΑ
I _{off}	Power Off Leakage Current	0	V _I or V _O = 5.5V		10		10	μA
I _{OZ}	High Impedance Output Leakage Current	2.7 to 3.6	$V_{I} = V_{IH} \text{ or } V_{IL}$ $V_{O} = 0 \text{ to } V_{CC}$		± 5		± 5	μA
I _{CC}	Quiescent Supply	2.7 to 3.6	$V_I = V_{CC} \text{ or } GND$		10		10	A
	Current		V_{I} or V_{O} = 3.6 to 5.5V		± 10		± 10	μA
ΔI_{CC}	I _{CC} incr. per Input	2.7 to 3.6	$V_{IH} = V_{CC} - 0.6V$		500		500	μΑ

Table 7: Dynamic Switching Characteristics

		Tes	Test Condition			Value			
Symbol	Parameter	v _{cc}		٦	Γ _A = 25 °0	C	Unit		
		(V)		Min.	Тур.	Max.			
V _{OLP}	Dynamic Low Level Quiet	3.3	C _L = 50pF V _{IL} = 0V, V _{IH} = 3.3V		0.8		V		
V _{OLV}	Output (note 1)	3.5	$V_{IL} = 0V, V_{IH} = 3.3V$		-0.8		v		

1) Number of outputs defined as "n". Measured with "n-1" outputs switching from HIGH to LOW or LOW to HIGH. The remaining output is measured in the LOW state.

Table	8:	AC	Electrical	Characteristics
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		Test Condition									
Symbol	Parameter	V _{cc}	CL	RL	$t_s = t_r$	-40 to	85 °C	-55 to	125 °C	Unit	
		(Ŭ) (pĒ)		(ns)	Min.	Max.	Min.	Max.			
t _{PLH} t _{PHL}	Propagation Delay	2.7				1.5	9.5	1.5	9.5		
	Time (CAB or CBA to An or Bn)	3.0 to 3.6	50	500	2.5	1.5	8.5	1.5	8.5	ns	
t _{PLH} t _{PHL}	Propagation Delay	2.7				1.5	8.0	1.5	8.0		
	Time (An to Bn or Bn to An)	3.0 to 3.6	50	500	2.5	1.5	7.0	1.5	7.0	ns	
t _{PLH} t _{PHL}	Propagation Delay	2.7				1.5	9.5	1.5	9.5		
	Time (SAB or SBA to An or Bn)	3.0 to 3.6	50	500	2.5	1.5	8.5	1.5	8.5	ns	
t _{PZL} t _{PZH}	t _{PZL} t _{PZH} Output Enable Time (G, DIR to An, Bn)	2.7	50	50 500	500	2.5	1.5	9.5	1.5	9.5	
		3.0 to 3.6		300	2.5	1.5	8.5	1.5	8.5	ns	
t _{PLZ} t _{PHZ}	Output Disable Time	2.7	50	500	2.5	1.5	9.5	1.5	9.5	ns	
	(G, DIR to An, Bn)	3.0 to 3.6	50	00 00	00 000	2.0	1.5	8.5	1.5	8.5	113
t _S	Setup Time, HIGH or	2.7					2.5		2.5		
	LOW level Data to CAB, CBA	3.0 to 3.6	50	500	2.5	2.5		2.5		ns	
t _h	Hold Time, HIGH or	2.7				1.5		1.5			
	LOW level Data to CAB, CBA	3.0 to 3.6	50	500	2.5	1.5		1.5		ns	
t _W	CAB, CBA Pulse	2.7				4.0		4.0			
	Width, HIGH or LOW	3.0 to 3.6	50	500	2.5	3.3		3.3		ns	
f _{MAX}	Clock Pulse Frequency	3.0 to 3.6	50	500	2.5	150		150		MHz	
t _{OSLH} t _{OSHL}	Output To Output Skew Time (note1, 2)	3.0 to 3.6	50	500	2.5		1.0		1.0	ns	

1) Skew is defined as the absolute value of the difference between the actual propagation delay for any two outputs of the same device switching in the same direction, either HIGH or LOW ($t_{OSLH} = |t_{PLHm} - t_{PLHn}|$, $t_{OSHL} = |t_{PHLm} - t_{PHLn}|$) 2) Parameter guaranteed by design

Table 9: Capacitive Characteristics

		Те					
Symbol	Parameter	V _{cc}		-	Γ _A = 25 °C	C	Unit
		(V)		Min.	Тур.	Max.	
C _{IN}	Input Capacitance	3.3	$V_{IN} = 0$ to V_{CC}		6		pF
C _{I/O}	I/O Capacitance	3.3	$V_{IN} = 0$ to V_{CC}		10		pF
C _{PD}	Power Dissipation Capacitance (note 1)	3.3	f _{IN} = 10MHz V _{IN} = 0 or V _{CC}		37		pF

1) C_{PD} is defined as the value of the IC's internal equivalent capacitance which is calculated from the operating current consumption without load. (Refer to Test Circuit). Average operating current can be obtained by the following equation. $I_{CC(opr)} = C_{PD} \times V_{CC} \times f_{IN} + I_{CC}/8$ (per circuit)

Figure 5: Test Circuit



	e p e n
t _{PZL} , t _{PLZ}	6V
t _{PZH} , t _{PHZ}	GND

 C_L = 50 pF or equivalent (includes jig and probe capacitance) R_L = R1 = 500 Ω or equivalent

 $\bar{R_T} = Z_{OUT}$ of pulse generator (typically 50 Ω)

Figure 6: Waveform - Propagation Delays, SAB, SBA, An, Bn, Times (f=1MHz; 50% duty cycle)





Figure 7: Waveform - Output Enable And Disable Time (f=1MHz; 50% duty cycle)

Figure 8: Waveform - Setup And Hold Time, CAB, CBA Maximum Frequency (f=1MHz; 50% duty cycle)



Figure 9: Waveform - Pulse Width (f=1MHz; 50% duty cycle)





SO-24 MECHANICAL DATA

DIM.		mm.		inch				
DIW.	MIN.	TYP	MAX.	MIN.	TYP.	MAX.		
А	2.35		2.65	0.093		0.104		
A1	0.1		0.30	0.004		0.012		
В	0.33		0.51	0.013		0.020		
С	0.23		0.32	0.009		0.013		
D	15.20		15.60	0.598		0.614		
E	7.4		7.6	0.291		0.299		
е		1.27			0.050			
Н	10.00		10.65	0.394		0.419		
h	0.25		0.75	0.010		0.030		
L	0.4		1.27	0.016		0.050		
k	0°		8°	0°		8°		
ddd			0.100			0.004		



TSSOP24 MECHANICAL DATA

DIM.	mm.			inch		
	MIN.	ТҮР	MAX.	MIN.	TYP.	MAX.
А			1.1			0.043
A1	0.05		0.15	0.002		0.006
A2		0.9			0.035	
b	0.19		0.30	0.0075		0.0118
С	0.09		0.20	0.0035		0.0079
D	7.7		7.9	0.303		0.311
E	4.3		4.5	0.169		0.177
е		0.65 BSC			0.0256 BSC	
Н	6.25		6.5	0.246		0.256
к	0°		8°	0°		8°
L	0.50		0.70	0.020		0.028



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Tape & Reel SO-24 MECHANICAL DATA

DIM.	mm.			inch		
	MIN.	ТҮР	MAX.	MIN.	TYP.	MAX.
А			330			12.992
С	12.8		13.2	0.504		0.519
D	20.2			0.795		
Ν	60			2.362		
Т			30.4			1.197
Ao	10.8		11.0	0.425		0.433
Во	15.7		15.9	0.618		0.626
Ko	2.9		3.1	0.114		0.122
Po	3.9		4.1	0.153		0.161
Р	11.9		12.1	0.468		0.476
Р	11.9		12.1	0.468		0.47



Tape & Reel TSSOP24 MECHANICAL DATA

DIM.	mm.			inch		
	MIN.	ТҮР	MAX.	MIN.	TYP.	MAX.
А			330			12.992
С	12.8		13.2	0.504		0.519
D	20.2			0.795		
Ν	60			2.362		
Т			22.4			0.882
Ao	6.8		7	0.268		0.276
Во	8.2		8.4	0.323		0.331
Ko	1.7		1.9	0.067		0.075
Po	3.9		4.1	0.153		0.161
Р	11.9		12.1	0.468		0.476



Table 10: Revision History

Date	Revision	Description of Changes
15-Sep-2004 6		Ordering Codes Revision - pag. 1.

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